

Form PTO-1449 (modified)
INFORMATION DISCLOSURE CITATION

Atty. Docket No.

Serial No.

1138-71

Applicant:
Tsang et al.

Filing Date

Group

Sheet 1 of 1

JCS11 U.S. PTO
09/144579



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Examiner Initial	Document Number	Date	Name
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Foreign Patent Documents

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<u>Loke</u>	Matsumoto, S., et al., "Ultralow Specific on Resistance UMOSFET with Trench Contacts for Source and Body Regions Realised by Selfaligned Process," Electronics Letters, 29 Aug. 1991, UK, vol. 27, no. 18, ISN 0013-5194, pages 1640-1642, XPOOO264480
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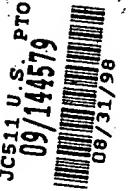
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Applicant: Tsang et al.		
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